### 2N2218 2N2218A

## SILICON NPN TRANSISTORS

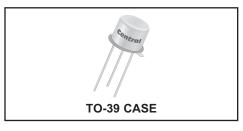


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# **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N2218 and 2N2218A are silicon NPN transistors manufactured by the epitaxial planar process, and designed for small signal general purpose and switching applications.





MAXIMUM	RATINGS: (T <sub>A</sub> =25°C unless otherwise	noted)				
	· A	SYMBOL	2N2218	2	N2218A	UNITS
Collector-Base Voltage		$V_{CBO}$	60		75	V
Collector-Emitter Voltage		$V_{CEO}$	30		40	V
Emitter-Base Voltage		$V_{EBO}$	5.0		6.0	V
Continuous Collector Current		IC	800			mA
Power Dissipation		$P_{D}$	800			mW
Power Dissipation (T <sub>C</sub> =25°C)		$P_{D}$	3.0			W
Operating and Storage Junction Temperature		$T_J$ , $T_{stg}$	-65 to +200		00	°C
ELECTRICAL CHARACTERISTICS: (T <sub>A</sub> =25°C)		2N22	2N2218 2N2218A			
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =50V	-	10	-	-	nA
I <sub>CBO</sub>	V <sub>CB</sub> =60V	-	-	-	10	nA
ICEV	$V_{CE}$ =60V, $V_{EB}$ =3.0V	-	-	-	10	nA
IEBO	V <sub>⊏R</sub> =3.0V	-	10	-	10	nA

ELECTRICAL CHARACTERISTICS: (T <sub>A</sub> =25°C)		218	2N2:	2N2218A	
TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
V <sub>CB</sub> =50V	-	10	-	-	nA
V <sub>CB</sub> =60V	-	-	-	10	nA
$V_{CE}$ =60V, $V_{EB}$ =3.0V	-	-	-	10	nA
V <sub>EB</sub> =3.0V	-	10	-	10	nA
$I_C=10\mu A$	60	-	75	-	V
I <sub>C</sub> =10mA	30	-	40	-	V
I <sub>E</sub> =10μA	5.0	-	6.0	-	V
I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	-	0.4	-	0.3	V
I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	-	1.6	-	1.0	V
I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	-	1.3	-	1.2	V
I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	-	2.6	-	2.0	V
$V_{CE}$ =10V, $I_{C}$ =100 $\mu$ A	20	-	20	-	
V <sub>CE</sub> =10V, I <sub>C</sub> =1.0mA	25	-	25	-	
$V_{CE}$ =10V, $I_{C}$ =10mA	35	-	35	-	
V <sub>CE</sub> =10V, I <sub>C</sub> =150mA	40	120	40	120	
$V_{CE}$ =1.0V, $I_{C}$ =150mA	20	-	20	-	
V <sub>CE</sub> =10V, I <sub>C</sub> =500mA	20	-	-	-	
$V_{CE}$ =10V, $I_{C}$ =500mA	-	-	25	-	
	TEST CONDITIONS  V <sub>CB</sub> =50V  V <sub>CB</sub> =60V  V <sub>CE</sub> =60V, V <sub>EB</sub> =3.0V  V <sub>EB</sub> =3.0V  I <sub>C</sub> =10µA  I <sub>C</sub> =10mA  I <sub>C</sub> =150mA, I <sub>B</sub> =15mA  I <sub>C</sub> =500mA, I <sub>B</sub> =50mA  I <sub>C</sub> =150mA, I <sub>B</sub> =15mA  I <sub>C</sub> =150mA, I <sub>B</sub> =15mA  I <sub>C</sub> =100µA  V <sub>CE</sub> =10V, I <sub>C</sub> =100µA  V <sub>CE</sub> =10V, I <sub>C</sub> =10mA  V <sub>CE</sub> =10V, I <sub>C</sub> =150mA  V <sub>CE</sub> =10V, I <sub>C</sub> =500mA	TEST CONDITIONS V <sub>CB</sub> =50V - V <sub>CB</sub> =60V - V <sub>CE</sub> =60V, V <sub>EB</sub> =3.0V - I <sub>C</sub> =10μA - I <sub>C</sub> =10μA - I <sub>C</sub> =10μA - I <sub>C</sub> =150mA, I <sub>B</sub> =15mA - I <sub>C</sub> =500mA, I <sub>B</sub> =50mA - I <sub>C</sub> =500mA, I <sub>B</sub> =50mA I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	TEST CONDITIONS         MIN         MAX           VCB=50V         -         10           VCB=60V, VEB=3.0V         -         -           VEB=3.0V         -         10           IC=10µA         60         -           IC=10mA         30         -           IC=10mA         5.0         -           IC=150mA, IB=15mA         -         0.4           IC=500mA, IB=50mA         -         1.6           IC=150mA, IB=50mA         -         1.3           IC=500mA, IB=50mA         -         2.6           VCE=10V, IC=100µA         20         -           VCE=10V, IC=100mA         25         -           VCE=10V, IC=150mA         40         120           VCE=1.0V, IC=150mA         20         -           VCE=10V, IC=500mA         20         -	TEST CONDITIONS         MIN         MAX         MIN           V <sub>CB</sub> =50V         -         10         -           V <sub>CB</sub> =60V         -         -         -           V <sub>CE</sub> =60V, V <sub>EB</sub> =3.0V         -         -         -           V <sub>EB</sub> =3.0V         -         10         -           I <sub>C</sub> =10µA         60         -         75           I <sub>C</sub> =10µA         5.0         -         6.0           I <sub>C</sub> =10µA         5.0         -         6.0           I <sub>C</sub> =150mA, I <sub>B</sub> =15mA         -         0.4         -           I <sub>C</sub> =500mA, I <sub>B</sub> =50mA         -         1.3         -           I <sub>C</sub> =500mA, I <sub>B</sub> =50mA         -         2.6         -           V <sub>C</sub> E=10V, I <sub>C</sub> =100µA         20         -         20           V <sub>C</sub> E=10V, I <sub>C</sub> =100mA         35         -         35           V <sub>C</sub> E=10V, I <sub>C</sub> =150mA         40         120         40           V <sub>C</sub> E=1.0V, I <sub>C</sub> =150mA         20         -         20           V <sub>C</sub> E=10V, I <sub>C</sub> =500mA         20         -         -         20	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

R1 (31-July 2013)

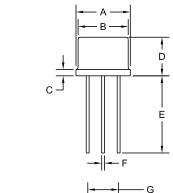
## 2N2218 2N2218A

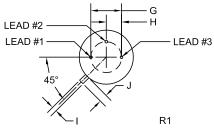




ELECTRICAL CHARACTERISTICS - Continued: (TA=25		2N2218		2N2218A			
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS	
f <sub>T</sub>	$V_{CE}$ =20 $V$ , $I_{C}$ =20 $M$	250	-	250	-	MHz	
C <sub>ob</sub>	$V_{CB}$ =10V, f=100kHz	-	8.0	-	8.0	pF	
ton	$V_{CC}$ =30V, $I_C$ =150mA, $I_B$ =15mA	-	35	-	35	ns	
toff	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA, I <sub>B1</sub> =I <sub>B2</sub> =15mA	-	285	-	285	ns	

# **TO-39 CASE - MECHANICAL OUTLINE**





DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
A (DIA)	0.335	0.370	8,51	9.40		
B (DIA)	0.315	0.335	8.00	8.51		
С	-	0.040	-	1.02		
D	0.240	0.260	6.10	6.60		
Е	0.500	-	12.70	-		
F (DIA)	0.016	0.021	0.41	0.53		
G (DIA)	0.200		5.08			
Н	0.100		2.54			
	0.028	0.034	0.71	0.86		
J	0.029	0.045	0.74	1.14		

TO-39 (REV: R1)

# LEAD CODE:

- 1) Emitter 2) Base
- 3) Collector

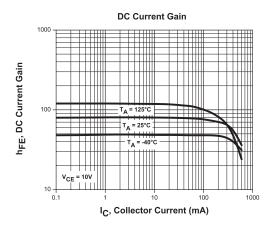
MARKING: FULL PART NUMBER

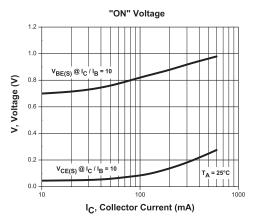
### 2N2218 2N2218A

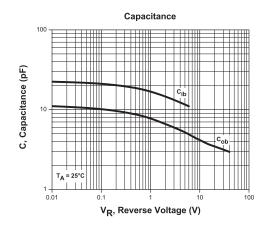
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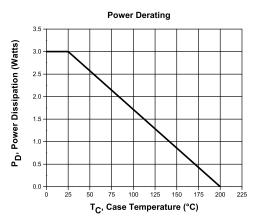


### TYPICAL ELECTRICAL CHARACTERISTICS









#### **OUTSTANDING SUPPORT AND SUPERIOR SERVICES**



#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

#### **DESIGNER SUPPORT/SERVICES**

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

#### REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

#### **CONTACT US**

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